

## Trans IGBT Chip N-CH 1600V 60A 312mW 3-Pin(3+Tab) TO-247 Tube

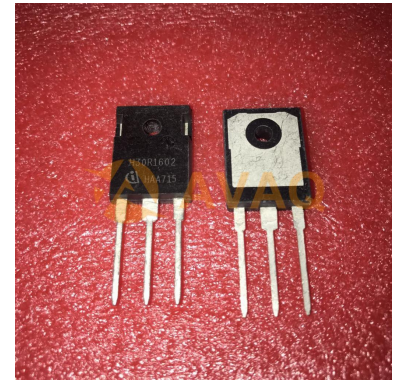
**Manufacturer:** [Infineon Technologies Corporation](#)

**Package/Case:** TO-247

**Product Type:** Thyristors

**RoHS:** RoHS Compliant/Lead free 

**Lifecycle:** Obsolete



Images are for reference only

[Inquiry](#)

### General Description

IHW30N160R2 is a specific model of Insulated Gate Bipolar Transistor (IGBT). It is a high-power semiconductor device used for controlling and amplifying electrical signals.

### Key Features

Maximum collector-emitter voltage of 1600V

Maximum collector current of 60A

Low collector-emitter saturation voltage

Fast switching speed

Low on-state resistance

Positive temperature coefficient for easy paralleling

### Application

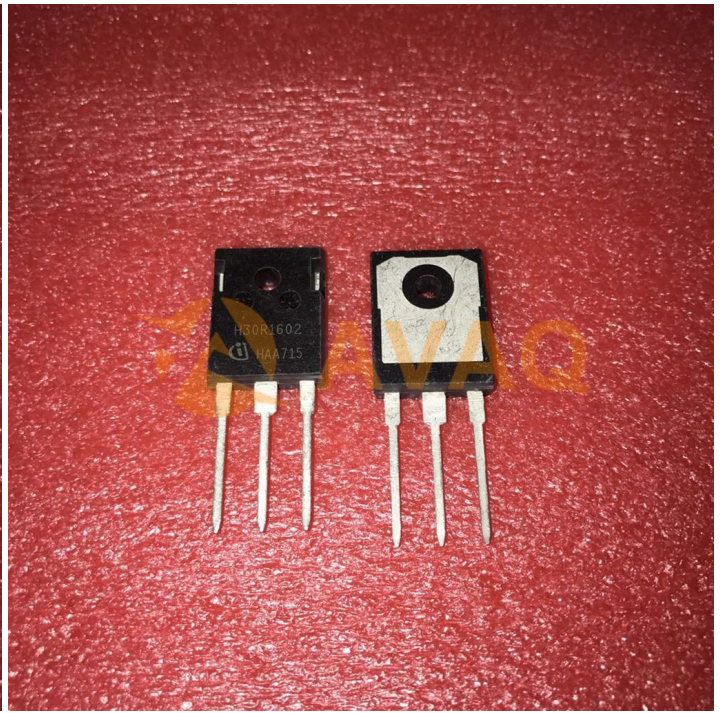
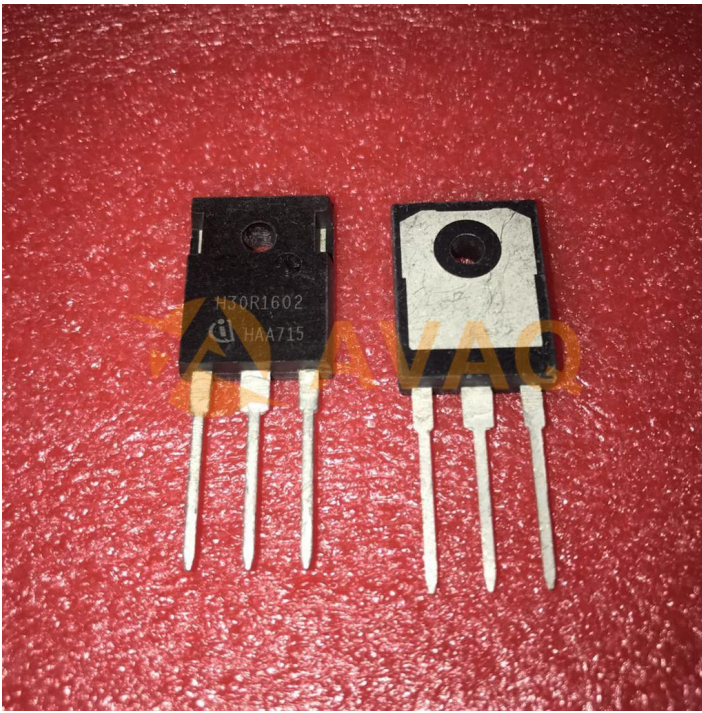
Motor drives

Switch-mode power supplies

Uninterruptible power supplies (UPS)

Welding equipment

Renewable energy systems



## Recommended For You

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### IHW20N135R3

Infineon Technologies Corporation

TO-247

### IHW15N120R3

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### IHW30N110R3

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### IHW20N135R5XKSA1

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### IHW25N120E1

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### IHW20N120R5

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### IHW20N135R5

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### IHW50N65R5

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### IHW30N135R5

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### IHW40N120R3

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### IHW40N60R

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### IHW40T60

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### IHW30N60T

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### IHW40N120R5XKSA1

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### IHW30N160R5XKSA1

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